FAST RECOVERY

RECTIFIERS

12 AMPERES

200 VOLTS



Switchmode Dual Fast Recovery Power Rectifiers

Designed for use in switching power supplies, inverters and as free wheeling diodes. These state-of-the-art devices have the following

Features

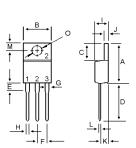
- *Low Reverse Leakage Current
- * Fast Switching for High Efficiency
- *150°C Operating Junction Temperature
- *Low Stored Charge Majority Carrier Conduction
- *Low Forward Voltage, High Current Capability
- * Plastic Material used Carries Underwriters Laboratory
- * Flammability Classification 94V-O
- *Pb free
- * In compliance with EU RoHs directives



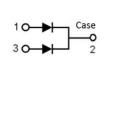


4PoH

TO-220AB



DIM	MILLIMETERS			
DIM	MIN	MAX		
Α	14.68	16.00		
В	9.78	10.42		
С	5.02	6.60		
D	13.00	14.62		
Е	3.10	4.19		
F	2.41	2.67		
G	1.10	1.67		
Н	0.69	1.01		
1	4.22	4.98		
J	1.14	1.40		
K	2.20	3.30		
L	0.28	0.61		
М	2.48	3.00		
0	3.50	4.00		



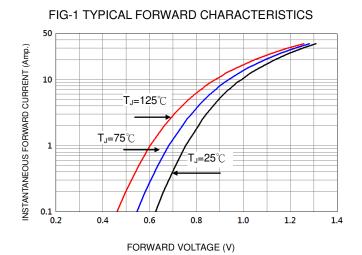
MAXIMUM RATINGS

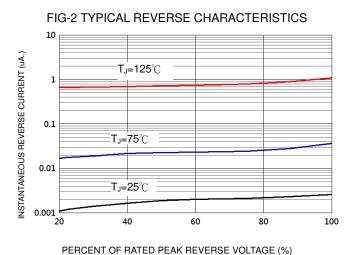
IVI/ (/ CIIVIOIVI I I/ CI II VAO		,	
Characteristic	Symbol	F12C20C	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RRM} \ V_{RWM} \ V_{R} \end{array}$	200	V
RMS Reverse Voltage	$V_{\text{R(RMS)}}$	140	٧
Average Rectifier Forward Current (per diode) Total Device (Rated V _R)	I _{F(AV)}	6 12	А
Peak Repetitive Forward Current (Rate V _R , Square Wave, 20kHz)	I _{FM}	12	Α
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions half-ware, single phase, 60Hz)	I _{FSM}	100	Α
Operating and Storage Junction Temperature Range	T_J , T_{stg}	-65 to +150	$^{\circ}\!\mathbb{C}$

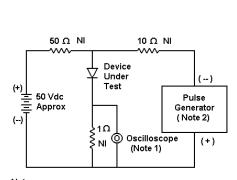
ELECTRICAL CHARACTERISTICS

LEEGTHIOAE GHARAGTERIGHOS							
Characteristic	Symbol	Min.	Тур.	Max.	Unit		
Maximum Instantaneous Forward Voltage ($I_F = 6 \text{ Amp } T_C = 25^{\circ}C$) ($I_F = 6 \text{ Amp } T_C = 125^{\circ}C$)	V _F		0.92 0.78	1.3	V		
Maximum Instantaneous Reverse Current (Rated DC Voltage, T _C = 25°C) (Rated DC Voltage, T _C = 125°C)	I _R		0.01 2.0	5 	uA		
Reverse Recovery Time ($I_F = 0.5 \text{ A}$, $I_R = 1.0$, $I_{rr} = 0.25 \text{ A}$)	T _{rr}		17	35	ns		
Typical Junction Capacitance (Reverse Voltage of 4 volts & f=1 MHz)	C _P		39		₽F		

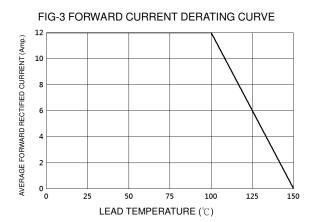


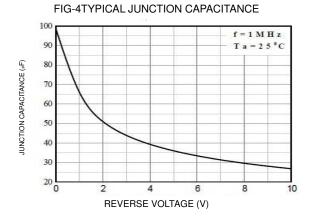


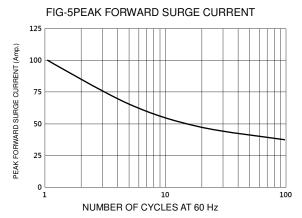


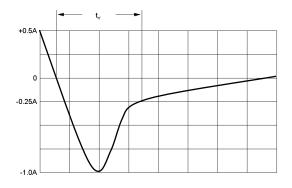


Notes: 1. Rise Time = 7 ns max. Input Impedance = 1 M Ω , 22 pF 2. Rise Time = 10 ns max. Input Impedance = 50Ω









Set time base for 20/50 ns/cm

FIG-6 Reverse Recovery Time Characteristic and Test Circuit Diagram



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